

### Abstract of the Disclosure

A method of manufacturing a transistor of a semiconductor device is provided. The method includes forming an N type gate pattern and a P type gate pattern on a substrate, implanting N type impurities into an N type transistor area, forming an insulation layer on the substrate including the N type gate pattern, forming a first spacer ~~is formed~~ on a sidewall of the P type gate pattern by partially etching the insulation layer in a P type transistor area, and implanting P type impurities into the P type gate pattern and into the P type transistor area, thereby forming a CMOS transistor on the substrate. Thus, damage to the substrate and the transistor is prevented, thereby improving electrical characteristics of the transistor.